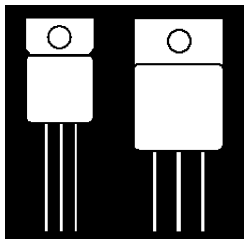


OM60N06SA OM60N05SA OM50N06ST
OM50N06SA OM50N05SA OM50N05ST

LOW VOLTAGE, LOW $R_{DS(on)}$ POWER MOSFETS IN HERMETIC ISOLATED PACKAGE



**50V And 60V Ultra Low $R_{DS(on)}$
Power MOSFETs In TO-257 And TO-254
Isolated Packages**

FEATURES

- Isolated Hermetic Metal Packages
- Ultra Low $R_{DS(on)}$
- Low Conductive Loss/Low Gate Charge
- Available Screened To MIL-S-19500, TX, TXV And S Levels
- Ceramic Feedthroughs Available

DESCRIPTION

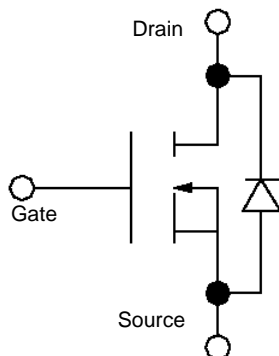
This series of hermetic packaged MOSFETs are ideally suited for low voltage applications; battery powered voltage power supplies, motor controls, dc to dc converters and synchronous rectification. The low conduction loss allows smaller heat sinking and the low gate charge simpler drive circuitry.

MAXIMUM RATINGS (Per Device)

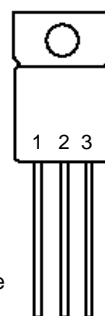
PART NO.	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Package
OM60N06SA	60	.025	60	TO-254AA
OM50N06SA	60	.030	50	TO-254AA
OM50N06ST	60	.035	50	TO-257AA
OM60N05SA	50	.025	60	TO-254AA
OM50N05SA	50	.030	50	TO-254AA
OM50N05ST	50	.035	50	TO-257AA

3.1

SCHEMATIC

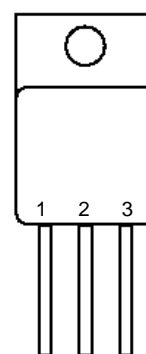


T-3 PIN CONNECTION



Pin 1: Drain
Pin 2: Source
Pin 3: Gate

M-PAK PIN CONNECTION



Pin 1: Drain
Pin 2: Source
Pin 3: Gate

OM60N06SA - OM50N05ST

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	60N06SA	50N06ST 50N05SA	60N05SA	50N05ST 50N05SA	Units	
V_{DS}	Drain-Source Voltage	60	60	50	50	V
V_{DGR}	Drain-Gate Voltage ($R_{GS} = 1\text{ M}\Omega$)	60	60	50	50	V
V_{GS}	Gate-Source Voltage, Continuous	± 20	± 20	± 20	± 20	V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current ²	55	50	55	50	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current ²	37	33	37	33	A
I_{DM}	Pulsed Drain Current ¹	220	200	220	200	A
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	100	100	100	100	W
$P_D @ T_C = 100^\circ\text{C}$	Maximum Power Dissipation	40	40	40	40	W
Junction-To-Case	Linear Derating Factor ¹	.80	.80	.80	.80	W/ $^\circ\text{C}$
T_J T_{stg}	Operating and Storage Temperature Range	-55 to 150	-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$
Lead Temperature	(1/16" from case for 10 secs.)	300	300	300	300	$^\circ\text{C}$

1 Pulse Test: Pulse width $\leq 300\ \mu\text{sec}$. Duty Cycle $\leq 1.5\%$.
 2 Package Limited SA $I_b = 25\text{ A}$, SC SC $I_b = 35\text{ A}$ @ 25°C

THERMAL RESISTANCE

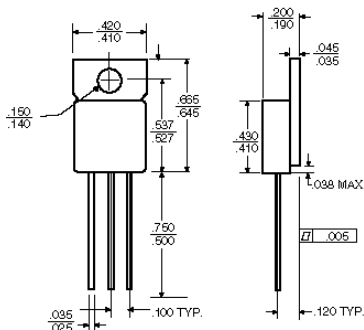
R_{thJC}	Junction-to-Case	1.25	$^\circ\text{C}/\text{W}$
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PACKAGE LIMITATIONS

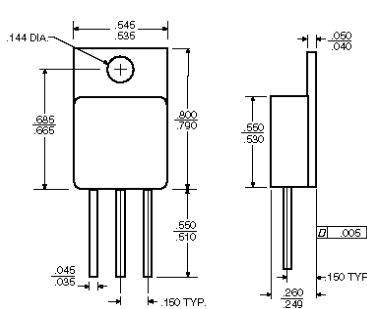
Parameters	TO254AA	TO-257AA	Unit	
I_D	Continuous Drain Current	25	15	A
	Linear Derating Factor, Junction-to-Ambient	.020	.015	W/ $^\circ\text{C}$
R_{thJA}	Thermal Resistance, Junction-to-Ambient (Free Air Operation)	50	65	$^\circ\text{C}/\text{W}$
	Linear Derating, Junction-to-Case	0.8	0.8	W/ $^\circ\text{C}$

3.1

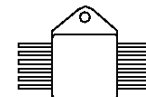
T-3 MECHANICAL OUTLINE



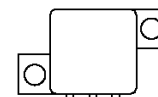
M-PAK MECHANICAL OUTLINE



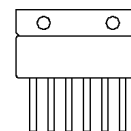
PACKAGE OPTIONS



MOD PAK



Z-TAB



6 PIN SIP

Notes:

- Standard Products are supplied with glass feedthroughs. For ceramic feedthroughs, add the letter "C" to the part number. Example - OMXXXXCSA.
- MOSFETs are also available in Z-Pak, dual and quad pak styles. Please call the factory for more information.



OM50N06SA (T_C = 25°C unless otherwise specified)

Avalanche Characteristics	Min.	Typ.	Max.	Units	Test Conditions
I _{AV} Avalanche Current			50	A	(repetitive or non-repetitive, T _J = 25°C)
E _{AS} Single Pulse Avalanche Energy			400	mJ	(starting T _J = 25°C, I _B = I _{AS} , V _{DS} = 25 V)
E _{RR} Repetitive Avalanche Energy			100	mJ	(pulse width limited by T _{Jmax} , δ < 1%)
I _{AR} Avalanche Current			30	A	(repetitive or non-repetitive, T _J = 100°C)
Electrical Characteristics - OFF					
V _{DRSS} Drain-Source Breakdown Voltage	60			V	I _B = 250 μA, V _{GS} = 0
I _{SS} Zero Gate Voltage Drain Current (V _{GS} = 0)			250 1000	μA	V _{DS} = Max. Rat. V _{GS} = Max. Rat. x 0.8, T _C = 125°C
I _{SSS} Gate-Body Leakage Current (V _{GS} = 0)			±100	nA	V _{DS} = ±20V
Electrical Characteristics - ON*					
V _{GS(th)} Gate Threshold Voltage		2	4	V	V _{GS} = V _{DS} , I _B = 250 μA
R _{DS(on)} Static Drain-Source On Resistance			.028 .086	Ω	V _{GS} = 10V, I _B = 25A T _C = 100°C
I _{DM(on)} On-State Drain Current			50	A	V _{GS} > I _{DM(on)} × R _{DS(on)} , V _{GS} = 10V
Electrical Characteristics - Dynamic					
g _{fs} Forward Transconductance			17	S	V _{GS} > I _{DM(on)} × R _{DS(on)} , I _B = 25A
C _{iss} Input Capacitance			2000	pF	V _{DS} = 25V
C _{oss} Output Capacitance			1000	pF	V _{GS} = 0
C _{res} Reverse Transfer Capacitance			300	pF	f = 1 MHz
Electrical Characteristics - Switching On					
T _{turn-on} Turn-On Time			45	nS	V _{DD} = 25V, I _B = 29A
t _r Rise Time			90	nS	R _G = 4.7 Ω, V _{GS} = 10V
(di/dt) _{on} Turn-On Current Slope			200	A/μS	V _{DD} = 40V, I _B = 50A
Q _g Total Gate Charge			45	nC	R _G = 50 Ω, V _{GS} = 10V V _{DD} = 40V, I _B = 50A, V _{GS} = 10V
Electrical Characteristics - Switching Off					
T _{turn-off} Turn-Off Time			160	nS	V _{DD} = 40V, I _B = 50A
t _f Fall Time			90	nS	R _G = 50 Ω, V _{GS} = 10V
t _{cross} Cross-Over Time			250	nS	
Electrical Characteristics - Source Drain Diode					
I _{SD} Source Drain Current			50	A	
I _{SDM} Source Drain Current (pulsed)			200	A	I _{SD} = 50A, V _{GS} = 0
V _{SD} Forward On Voltage			2	V	I _{SD} = 50A, di/dt = 100 A/μs
t _r Reverse Recovery Time			150	nS	V _R = 30V, T _J = 150°C
Q _r Reverse Recovery Charge			0.2	μC	
I _{FRM} Reverse Recovery Current			4	A	

*Pulsed: Pulse Duration ≤ 300μs, Duty Cycle ≤ 1.5%.

OM60N06SA (T_C = 25°C unless otherwise specified)

Avalanche Characteristics	Min.	Typ.	Max.	Units	Test Conditions
I _{AV} Avalanche Current			55	A	(repetitive or non-repetitive, T _J = 25°C)
E _{AS} Single Pulse Avalanche Energy			520	mJ	(starting T _J = 25°C, I _B = I _{AS} , V _{DD} = 25 V)
E _{RR} Repetitive Avalanche Energy			130	mJ	(pulse width limited by T _{Jmax} , δ < 1%)
I _{AR} Avalanche Current			34	A	(repetitive or non-repetitive, T _J = 100°C)
Electrical Characteristics - OFF					
V _{DRSS} Drain-Source Breakdown Voltage	60			V	I _B = 250 μA, V _{GS} = 0
I _{SS} Zero Gate Voltage Drain Current (V _{GS} = 0)			250 1000	μA	V _{DS} = Max. Rat. V _{GS} = Max. Rat. x 0.8, T _C = 125°C
I _{SSS} Gate-Body Leakage Current (V _{GS} = 0)			±100	nA	V _{DS} = ±20V
Electrical Characteristics - ON*					
V _{GS(th)} Gate Threshold Voltage		2	4	V	V _{GS} = V _{DS} , I _B = 250 μA
R _{DS(on)} Static Drain-Source On Resistance			.025 .060	Ω	V _{GS} = 10V, I _B = 30A T _C = 100°C
I _{DM(on)} On-State Drain Current			55	A	V _{GS} > I _{DM(on)} × R _{DS(on)} , V _{GS} = 10V
Electrical Characteristics - Dynamic					
g _{fs} Forward Transconductance			16	S	V _{GS} > I _{DM(on)} × R _{DS(on)} , I _B = 30A
C _{iss} Input Capacitance			2500	pF	V _{DS} = 25V
C _{oss} Output Capacitance			960	pF	V _{GS} = 0
C _{res} Reverse Transfer Capacitance			250	pF	f = 1 MHz
Electrical Characteristics - Switching On					
T _{turn-on} Turn-On Time			110	nS	V _{DD} = 25V, I _B = 55A
t _r Rise Time			300	nS	R _G = 50 Ω, V _{GS} = 10V
(di/dt) _{on} Turn-On Current Slope			160	A/μS	V _{DD} = 40V, I _B = 55A
Q _g Total Gate Charge			65	nC	R _G = 50 Ω, V _{GS} = 10V V _{DD} = 25V, I _B = 30A, V _{GS} = 10V
Electrical Characteristics - Switching Off					
T _{turn-off} Turn-Off Time			160	nS	V _{DD} = 40V, I _B = 55A
t _f Fall Time			160	nS	R _G = 50 Ω, V _{GS} = 10V
t _{cross} Cross-Over Time			320	nS	
Electrical Characteristics - Source Drain Diode					
I _{SD} Source Drain Current			55	A	
I _{SDM} Source Drain Current (pulsed)			200	A	I _{SD} = 55A, V _{GS} = 0
V _{SD} Forward On Voltage			1.6	V	I _{SD} = 55A, di/dt = 100 A/μs
t _r Reverse Recovery Time			100	nS	V _R = 25V, T _J = 150°C
Q _r Reverse Recovery Charge			.25	μC	
I _{FRM} Reverse Recovery Current			5	A	

*Pulsed: Pulse Duration ≤ 300μs, Duty Cycle ≤ 1.5%.



OM50N06ST (T_C = 25°C unless otherwise specified)

Avalanche Characteristics	Min.	Typ.	Max.	Units	Test Conditions
I _{AV} Avalanche Current			50	A	(repetitive or non-repetitive, T _J = 25°C)
E _{AS} Single Pulse Avalanche Energy			400	mJ	(starting T _J = 25°C, I _B = I _{SM} , V _{DS} = 25 V)
E _{REP} Repetitive Avalanche Energy			100	mJ	(pulse width limited by T _{Jmax} , δ < 1%)
I _{VP} Avalanche Current			30	A	(repetitive or non-repetitive, T _J = 100°C)
Electrical Characteristics - OFF					
V _{DS(ON)} Drain-Source Breakdown Voltage	60			V	I _B = 250 μA, V _{GS} = 0
I _{DSS} Zero Gate Voltage Drain Current (V _{GS} = 0)		250		μA	V _{DS} = Max Flat
I _{DSS} Gate-Body Leakage Current (V _{GS} = 0)		1000		μA	V _{DS} = Max Flat x 0.8, T _C = 125°C
I _{DSS} Current (V _{GS} = 0)		±100		nA	V _{DS} = ±20 V
Electrical Characteristics - ON					
V _{GS(th)} Gate Threshold Voltage	2		4	V	V _{DS} = V _{GS} , I _B = 250 μA
R _{DS(on)} Static Drain-Source On Resistance		.033		Ω	V _{GS} = 10 V, I _B = 25 A
R _{DS(on)} Resistance		.066		Ω	T _C = 100°C
I _{D(on)} On State Drain Current	50			A	V _{GS} > I _{DM} x R _{DS(on)} , V _{DS} = 10 V
Electrical Characteristics - Dynamic					
g _{fs} Forward Transconductance	17			S	V _{GS} > I _{DM} x R _{DS(on)} , I _B = 25 A
C _{iss} Input Capacitance	2000			pF	V _{GS} = 25 V
C _{oss} Output Capacitance	1000			pF	V _{GS} = 0
C _{res} Reverse Transfer Capacitance	300			pF	f = 1 MHz
Electrical Characteristics - Switching On					
T _{don} Turn-On Time	45			nS	V _{DS} = 25 V, I _B = 25 A
t _r Rise Time	90			nS	R _G = 4.7 Ω, V _{GS} = 10 V
(di/dt) _{on} Turn-On Current Slope	200			A/μS	V _{DS} = 40 V, I _B = 50 A
Q _g Total Gate Charge	45			nC	R _G = 50 Ω, V _{GS} = 10 V
Electrical Characteristics - Switching Off					
T _{off} Off Voltage Rise Time	160			nS	V _{DS} = 40 V, I _B = 50 A
t _f Fall Time	90			nS	R _G = 50 Ω, V _{GS} = 10 V
t _{cross} Cross-Over Time	250			nS	
Electrical Characteristics - Source Drain Diode					
I _{SD} Source Drain Current		50		A	I _{SP} = 50 A, V _{GS} = 0
I _{SM} Source Drain Current (pulsed)		200		A	
V _{SD} Forward On Voltage		2		V	I _{SD} = 50 A, V _{GS} = 0
t _r Reverse Recovery Time		150		nS	I _{SD} = 50 A, di/dt = 100 A/μs
Q _r Reverse Recovery Charge		0.2		μC	V _R = 30 V, T _J = 150°C
I _{FRM} Reverse Recovery Current		4		A	

*Pulsed: Pulse Duration ≤ 300μs, Duty Cycle ≤ 1.5%.

OM60N06SA (T_C = 25°C unless otherwise specified)

Avalanche Characteristics	Min.	Typ.	Max.	Units	Test Conditions
I _{AV} Avalanche Current			55	A	(repetitive or non-repetitive, T _J = 25°C)
E _{AS} Single Pulse Avalanche Energy			520	mJ	(starting T _J = 25°C, I _B = I _{SM} , V _{DS} = 25 V)
E _{REP} Repetitive Avalanche Energy			130	mJ	(pulse width limited by T _{Jmax} , δ < 1%)
I _{VP} Avalanche Current			34	A	(repetitive or non-repetitive, T _J = 100°C)
Electrical Characteristics - OFF					
V _{DS(ON)} Drain-Source Breakdown Voltage	50			V	I _B = 250 μA, V _{GS} = 0
I _{DSS} Zero Gate Voltage Drain Current (V _{GS} = 0)		250		μA	V _{DS} = Max Flat
I _{DSS} Gate-Body Leakage Current (V _{GS} = 0)		1000		μA	V _{DS} = Max Flat x 0.8, T _C = 125°C
I _{DSS} Current (V _{GS} = 0)		±100		nA	V _{DS} = ±20 V
Electrical Characteristics - ON					
V _{GS(th)} Gate Threshold Voltage	2		4	V	V _{DS} = V _{GS} , I _B = 250 μA
R _{DS(on)} Static Drain-Source On Resistance		.025		Ω	V _{GS} = 10 V, I _B = 30 A
R _{DS(on)} Resistance		.050		Ω	T _C = 100°C
I _{D(on)} On State Drain Current	55			A	V _{GS} > I _{DM} x R _{DS(on)} , V _{DS} = 10 V
Electrical Characteristics - Dynamic					
g _{fs} Forward Transconductance	16			S	V _{GS} > I _{DM} x R _{DS(on)} , I _B = 30 A
C _{iss} Input Capacitance	2500			pF	V _{GS} = 25 V
C _{oss} Output Capacitance	950			pF	V _{GS} = 0
C _{res} Reverse Transfer Capacitance	250			pF	f = 1 MHz
Electrical Characteristics - Switching On					
T _{don} Turn-On Time	110			nS	V _{DS} = 25 V, I _B = 55 A
t _r Rise Time	300			nS	R _G = 50 Ω, V _{GS} = 10 V
(di/dt) _{on} Turn-On Current Slope	160			A/μS	V _{DS} = 40 V, I _B = 55 A
Q _g Total Gate Charge	65			nC	R _G = 50 Ω, V _{GS} = 10 V
Electrical Characteristics - Switching Off					
T _{off} Off Voltage Rise Time	160			nS	V _{DS} = 40 V, I _B = 55 A
t _f Fall Time	160			nS	R _G = 50 Ω, V _{GS} = 10 V
t _{cross} Cross-Over Time	320			nS	
Electrical Characteristics - Source Drain Diode					
I _{SD} Source Drain Current		55		A	I _{SP} = 55 A, V _{GS} = 0
I _{SM} Source Drain Current (pulsed)		200		A	
V _{SD} Forward On Voltage		1.6		V	I _{SD} = 55 A, V _{GS} = 0
t _r Reverse Recovery Time		100		nS	I _{SD} = 55 A, di/dt = 100 A/μs
Q _r Reverse Recovery Charge		25		μC	V _R = 25 V, T _J = 150°C
I _{FRM} Reverse Recovery Current		5		A	

*Pulsed: Pulse Duration ≤ 300μs, Duty Cycle ≤ 1.5%.

OM50N05ST (T_C = 25°C unless otherwise specified)

Avalanche Characteristics	Min.	Typ.	Max.	Units	Test Conditions
I _{AV} Avalanche Current			50	A	(repetitive or non-repetitive, T _J = 25°C)
E _{AS} Single Pulse Avalanche Energy			400	mJ	(starting T _J = 25°C, I _B = I _{AV} , V _{DP} = 25 V)
E _{AR} Repetitive Avalanche Energy			100	mJ	(pulse width limited by T _{Jmax} , δ < 1%)
I _{AV} Avalanche Current			30	A	(repetitive or non-repetitive, T _J = 100°C)
Electrical Characteristics - OFF					
V _{DRSS} Drain-Source Breakdown Voltage	50			V	I _B = 250 μA, V _{GS} = 0
I _{ZSS} Zero Gate Voltage Drain Current (V _{GS} = 0)			250 1000	μA	V _{DS} = Max. Rat. V _{GS} = Max. Rat. x 0.8, T _C = 125°C
I _{GSS} Gate-Body Leakage Current (V _{GS} = 0)			±100	nA	V _{GS} = ±20 V
Electrical Characteristics - ON*					
V _{GS(th)} Gate Threshold Voltage	2		4	V	V _{GS} = V _{DS} , I _B = 250 μA
R _{DS(on)} Static Drain-Source On Resistance			.038 .066	Ω	V _{GS} = 10 V, I _B = 25 A T _C = 100°C
I _{DM} On-State Drain Current	50			A	V _{GS} > I _{DM} x R _{DS(on)} , V _{GS} = 10 V
Electrical Characteristics - Dynamic					
g _{fs} Forward Transconductance	17			S	V _{GS} > I _{DM} x R _{DS(on)} , I _B = 25 A
C _{iss} Input Capacitance		2000		pF	V _{GS} = 25 V
C _{oss} Output Capacitance		1000		pF	V _{GS} = 0
C _{res} Reverse Transfer Capacitance		300		pF	f = 1 MHz
Electrical Characteristics - Switching On					
T _{turn-on} Turn-On Time		45		nS	V _{DP} = 25 V, I _B = 29 A
t _r Rise Time		90		nS	R _G = 4.7 Ω, V _{GS} = 10 V
(di/dt) _{on} Turn-On Current Slope		200		A/μS	V _{DP} = 40 V, I _B = 50 A
Q _g Total Gate Charge		45		nC	R _G = 50 Ω, V _{GS} = 10 V V _{DP} = 40 V, I _B = 50 A, V _{GS} = 10 V
Electrical Characteristics - Switching Off					
T _{turn-off} Off Voltage Fall Time		160		nS	V _{DP} = 40 V, I _B = 50 A
t _f Fall Time		90		nS	R _G = 50 Ω, V _{GS} = 10 V
t _{cross} Cross-Over Time		250		nS	
Electrical Characteristics - Source Drain Diode					
I _{SD} Source Drain Current			50	A	
I _{SDM} Source Drain Current (pulsed)			200	A	
V _{SD} Forward On Voltage			2	V	I _{SD} = 50 A, V _{GS} = 0
t _r Reverse Recovery Time			150	nS	I _{SD} = 50 A, di/dt = 100 A/μs V _R = 30 V, T _J = 150°C
Q _r Reverse Recovery Charge			0.2	μC	
I _{RRM} Reverse Recovery Current			4	A	

*Pulsed: Pulse Duration ≤ 300μS, Duty Cycle ≤ 1.5%.

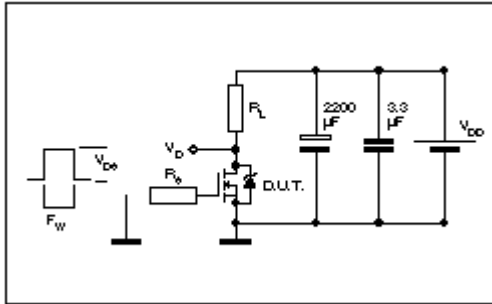
OM50N05SA (T_C = 25°C unless otherwise specified)

Avalanche Characteristics	Min.	Typ.	Max.	Units	Test Conditions
I _{AV} Avalanche Current			50	A	(repetitive or non-repetitive, T _J = 25°C)
E _{AS} Single Pulse Avalanche Energy			400	mJ	(starting T _J = 25°C, I _B = I _{AV} , V _{DP} = 25 V)
E _{AR} Repetitive Avalanche Energy			100	mJ	(pulse width limited by T _{Jmax} , δ < 1%)
I _{AV} Avalanche Current			30	A	(repetitive or non-repetitive, T _J = 100°C)
Electrical Characteristics - OFF					
V _{DRSS} Drain-Source Breakdown Voltage	50			V	I _B = 250 μA, V _{GS} = 0
I _{ZSS} Zero Gate Voltage Drain Current (V _{GS} = 0)			250 1000	μA	V _{DS} = Max. Rat. V _{GS} = Max. Rat. x 0.8, T _C = 125°C
I _{GSS} Gate-Body Leakage Current (V _{GS} = 0)			±100	nA	V _{GS} = ±20 V
Electrical Characteristics - ON*					
V _{GS(th)} Gate Threshold Voltage	2		4	V	V _{GS} = V _{DS} , I _B = 250 μA
R _{DS(on)} Static Drain-Source On Resistance			.028 .056	Ω	V _{GS} = 10 V, I _B = 25 A T _C = 100°C
I _{DM} On-State Drain Current	50			A	V _{GS} > I _{DM} x R _{DS(on)} , V _{GS} = 10 V
Electrical Characteristics - Dynamic					
g _{fs} Forward Transconductance	17			S	V _{GS} > I _{DM} x R _{DS(on)} , I _B = 25 A
C _{iss} Input Capacitance		2000		pF	V _{GS} = 25 V
C _{oss} Output Capacitance		1000		pF	V _{GS} = 0
C _{res} Reverse Transfer Capacitance		300		pF	f = 1 MHz
Electrical Characteristics - Switching On					
T _{turn-on} Turn-On Time		45		nS	V _{DP} = 25 V, I _B = 29 A
t _r Rise Time		90		nS	R _G = 4.7 Ω, V _{GS} = 10 V
(di/dt) _{on} Turn-On Current Slope		200		A/μS	V _{DP} = 40 V, I _B = 50 A
Q _g Total Gate Charge		45		nC	R _G = 50 Ω, V _{GS} = 10 V V _{DP} = 40 V, I _B = 50 A, V _{GS} = 10 V
Electrical Characteristics - Switching Off					
T _{turn-off} Off Voltage Fall Time		160		nS	V _{DP} = 40 V, I _B = 50 A
t _f Fall Time		90		nS	R _G = 50 Ω, V _{GS} = 10 V
t _{cross} Cross-Over Time		250		nS	
Electrical Characteristics - Source Drain Diode					
I _{SD} Source Drain Current			50	A	
I _{SDM} Source Drain Current (pulsed)			200	A	
V _{SD} Forward On Voltage			2	V	I _{SD} = 50 A, V _{GS} = 0
t _r Reverse Recovery Time			150	nS	I _{SD} = 50 A, di/dt = 100 A/μs V _R = 30 V, T _J = 150°C
Q _r Reverse Recovery Charge			0.2	μC	
I _{RRM} Reverse Recovery Current			4	A	

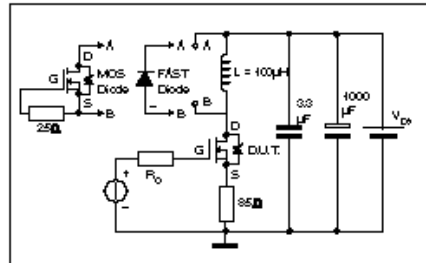
*Pulsed: Pulse Duration ≤ 300μS, Duty Cycle ≤ 1.5%.



Switching Times Test Circuits For Resistive Load

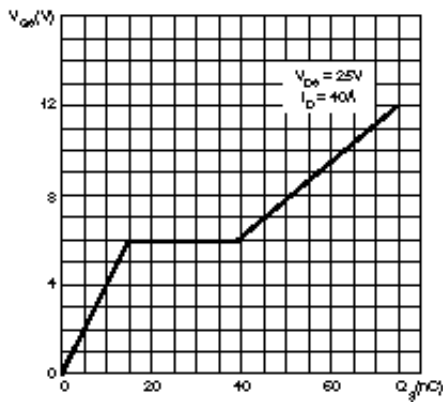


Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time

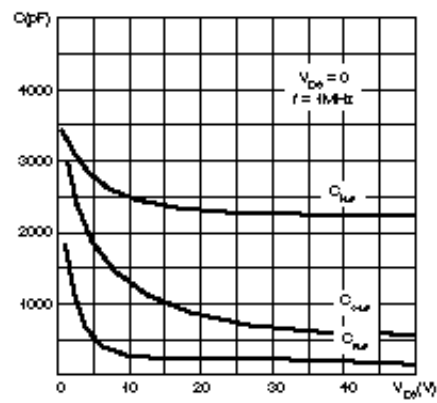


TYPICAL CHARACTERISTICS

Gate Charge vs Gate-Source Voltage

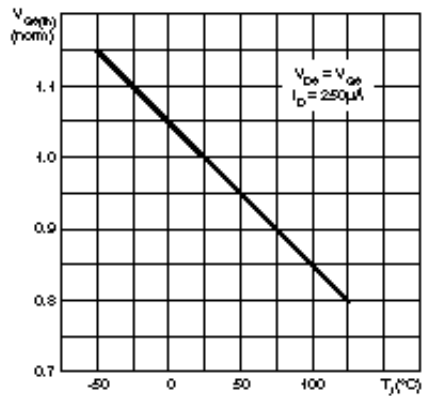


Capacitance Variations



3.1

Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature

